

10/708,907

IN THE CLAIMS:

Please cancel claims 15-20 and 26-39 without prejudice or disclaimer.

1. (Original) An integrated circuit structure comprising:
a substrate having at least two types of crystalline orientations;
first-type transistors formed on first portions of said substrate having a first type of crystalline orientation; and
second-type transistors formed on second portions of said substrate having a second type of crystalline orientation,
wherein selected ones of said first portions of said substrate comprise non-floating substrate portions, and
wherein remaining ones of said first portions and all of said second portions of said substrate comprise floating substrate portions.
2. (Original) The structure in claim 1, wherein said floating structures comprise silicon over insulator (SOI) structures.
3. (Original) The structure in claim 1, wherein said non-floating substrate portions are biased by layers below said substrate.
4. (Original) The structure in claim 1, further comprising a complete insulator below said floating substrate portions.
5. (Original) The structure in claim 1, further comprising an incomplete insulator below said non-floating substrate portions.
6. (Original) The structure in claim 1, further comprising shallow trench isolation (STI) regions between said non-floating substrate portions and said floating substrate portions.

10/708,907

7. (Original) The structure in claim 1, wherein each of said second portions of said substrate includes a plurality of floating substrate portions.
8. (Original) An integrated circuit structure comprising:
 - a substrate having at least two types of crystalline orientations;
 - N-type transistors formed on first portions of said substrate having a first type of crystalline orientation; and
 - P-type transistors formed on second portions of said substrate having a second type of crystalline orientation,
 - wherein selected ones of said first portions of said substrate comprise non-floating substrate portions, and
 - wherein remaining ones of said first portions and all of said second portions of said substrate comprise floating substrate portions.
9. (Original) The structure in claim 8, wherein said floating structures comprise silicon over insulator (SOI) structures.
10. (Original) The structure in claim 8, wherein said non-floating substrate portions are biased by layers below said substrate.
11. (Original) The structure in claim 8, further comprising a complete insulator below said floating substrate portions.
12. (Original) The structure in claim 8, further comprising an incomplete insulator below said non-floating substrate portions.
13. (Original) The structure in claim 8, further comprising shallow trench isolation (STI) regions between said non-floating substrate portions and said floating substrate portions.

10/708,907

14. (Original) The structure in claim 8, wherein each of said second portions of said substrate includes a plurality of floating substrate portions.

15-20 (Cancelled).

21. (Original) An integrated circuit structure comprising:

a substrate comprising a material having one type of crystalline orientation, wherein said substrate includes first portions and second portions, wherein the crystalline structure of said first portions is rotated with respect to the crystalline structure of said second portions;

first-type fin-type field effect transistors (FinFETs) formed on said first portions of said substrate; and

second-type FinFETs formed on said second portions of said substrate,

wherein said first-type FinFETs have fins that are parallel to fins of said second-type FinFETs.

22. (Original) The structure in claim 21, wherein said substrate comprises a floating substrate.

23. (Original) The structure in claim 22, wherein said first-type FinFETs and said second-type FinFETs comprise silicon over insulator (SOI) structures.

24. (Original) The structure in claim 22, further comprising a complete insulator below said floating substrate.

25. (Original) The structure in claim 22, further comprising shallow trench isolation (STI) regions between said first portions of said substrate and said second portions of said substrate.

26-39 (Cancelled).